



5-V FULL-DUPLEX RS-485/RS-422 DRIVER AND BALANCED RECEIVER

FEATURES

- Designed for INTERBUS Applications
- Balanced Receiver Thresholds
- 1/2 Unit-Load (up to 64 nodes on the bus)
- Bus-Pin ESD Protection 15 kV HBM
- Bus-Fault Protection of –7V to 12V
- Thermal Shutdown Protection
- Power-Up/Down Glitch-free Bus Inputs and Outputs
- Designed for RS-422 and RS-485 Networks

APPLICATIONS

- Digital Motor Control
- Utility Meters
- Chassis-to-Chassis Interconnections
- Electronic Security Stations
- Industrial, Process, and Building Automation
- Point-of-Sale (POS) Terminals and Networks
- DTE/DCE Interfaces

DESCRIPTION

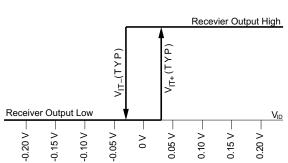
The SN65HVD179 is a differential line driver and differential-input line receiver that operates with a 5-V power supply. Each driver and receiver has separate input and output pins for full-duplex bus communication designs. They are designed for balanced transmission lines and interoperation with ANSI TIA/EIA-485A, TIA/EIA-422-B, ITU-T v.11, and ISO 8482:1993 standard-compliant devices.

The differential bus driver and receiver are monolithic, integrated circuits designed for full-duplex bi-directional data communication on multipoint bus-transmission lines at signaling rates⁽¹⁾ up to 25 Mbps. The SN65HVD179 is fully enabled with no external enabling pins.

The 1/2 unit load receiver has a high receiver input resistance. This results in lower bus leakage currents over the common-mode voltage range, and reduces the total amount of current that a 485 driver is forced to source or sink when transmitting.

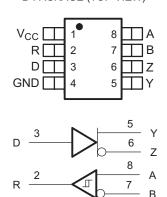
The balanced differential receiver input threshold makes the SN65HVD179 fully compatible with fieldbus requirements that define an external failsafe structure.

 The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).



BALANCED RECEIVER INPUT THRESHOLDS





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

SIGNALING RATE	UNIT LOADS	BASE PART NUMBER	SOIC MARKING
25 Mbps	1/2	SN65HVD179	SN65HVD179

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

		UNIT
V _{CC}	Supply voltage range	–0.3 V to 6 V
V_A,V_B,V_Y,V_Z	Voltage range at any bus terminal (A, B, Y, Z)	–9 V to 14 V
V _{TRANS}	Voltage input, transient pulse through 100 $\Omega.$ See Figure 8 (A, B, Y, Z) $^{(3)}$	–50 to 50 V
VI	Voltage input range (D, DE, RE)	–0.5 V to 7 V
P _{CONT}	Continuous total power dissipation	Internally limited ⁽⁴⁾
I _O	Output current (receiver output only, R)	11 mA

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

This tests survivability only and the output state of the receiver is not specified. (3)

(4)The Thermal shutdown of this device internally limits the continuous total power dissipation. Thermal shutdown typically occurs when the junction temperature reaches 165°C.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		4.5		5.5	V
$V_{\text{I}} \text{ or } V_{\text{IC}}$	Voltage at any bus terminal	(separately or common mode)	-7 ⁽¹⁾		12	v
1/t _{UI}	Signaling rate				25	Mbps
RL	Differential load resistance		54	60		Ω
V _{IH}	High-level input voltage	D	2		V_{CC}	
V _{IL}	Low-level input voltage	D	0		0.8	V
V _{ID}	Differential input voltage		-12		12	
	Lligh lovel output ourrent	Driver	-60			س ۸
IOH	High-level output current	Receiver	-8			mA
		Driver			60	س ۸
I _{OL}	Low-level output current	Receiver			8	mA
TJ	Junction temperature ⁽²⁾		-40		150	°C

The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet. (1)

See thermal characteristics table for information regarding this specification. (2)

ELECTROSTATIC DISCHARGE PROTECTION

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
Human body model	Bus terminals and GND		±16		
Human body model ⁽²⁾	All pins		±4		kV
Charged-device-model ⁽³⁾	All pins		±1		

All typical values at 25°C and with a 5-V supply. (1)

Tested in accordance with JEDEC Standard 22, Test Method A114-A. Tested in accordance with JEDEC Standard 22, Test Method C101. (2)

(3)



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DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER		TEST	CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{I(K)}	Input clamp voltage		I _I = -18 mA		-1.5			
			I _O = 0		4		V_{CC}	
	Standy atota differentia		$R_L = 54 \Omega$, See Fig	jure 1 (RS-485)	1.7	2.6		
V _{OD(SS)}	Steady-state differentia	i oulput voltage	$R_L = 100 \Omega$, See F	igure 1 (RS-422)	2.4	3.2		V
			$V_{\text{test}} = -7 \text{ V to } 12 \text{ V}$	/, See Figure 2	1.6			
$\Delta V_{\text{OD}(SS)} $	Change in magnitude o differential output voltag	,	$R_L = 54 \Omega$, See Fig	ure 1 and Figure 2	-0.2		0.2	
V _{OD(RING)}	Differential Output Volta undershoot	age overshoot and	$R_L = 54 \Omega, C_L = 50$ Figure 3 for definiti	pF, See Figure 5 and on			10% ⁽²⁾	
V _{OC(PP)}	Peak-to-peak common-	mode output voltage			0.5			1
V _{OC(SS)}	Steady-state common-r	node output voltage	See Figure 4		2.2		3.3	V
$\Delta V_{OC(SS)}$	Change in steady-state output voltage	common-mode	See Figure 4		-0.1		0.1	·
$I_{Z(Z)}$ or	l link immedence state		$V_{CC} = 0 V, V_Z \text{ or } V$ Other input at 0 V	_Y = 12 V,			90	
$I_{Y(Z)}$	High-impedance state of	Sulput current	$V_{CC} = 0 V, V_Z \text{ or } V$ Other input at 0 V	$_{\rm Y} = -7 {\rm V},$	-10			μA
$I_{Z(S)}$ or	Short Circuit output our	root(3)	V_Z or $V_Y = -7 V$	Other input	-250		250	
$I_{Y(S)}$	Short Circuit output cur	rent(*)	V_Z or $V_Y = 12 V$	at 0 V	-250		250	mA
l _l	Input current	$V_{I} = 0, V_{I} = 2$			0		100	μA
C _(OD)	Differential output capa	citance				16		pF

All typical values are at 25°C and with a 5-V supply.
 10% of the peak-to-peak Differential Output voltage swing, per TIA/EIA-485.

(3) Under some conditions of short-circuit to negative voltages, output currents exceeding the ANSI TIA/EIA-485-A maximum current of 250 mA may occur. Continuous exposure may affect device reliability.

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		4	0	10	
t _{PHL}	Propagation delay time, high-to-low-level output	$R_{L} = 54 \Omega, C_{L} = 50 pF,$	4	8	12	ns
t _r	Differential output signal rise time	See Figure 5	0	6	12	
t _f	Differential output signal fall time		3			ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})			1.4		ns
t _{sk(pp)} ⁽²⁾	Part-to-part skew			1		ns

(1)

All typical values are at 25°C and with a 5-V supply. $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. (2)

INSTRUMENTS

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RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST COND	ITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
$V_{\text{IT}+}$	Positive-going differential input threshold voltage	$I_{O} = -8 \text{ mA}$ $I_{O} = 8 \text{ mA}$				0.2	M
V _{IT-}	Negative-going differential input threshold voltage			-0.2			V
V _{hys}	Hysteresis voltage $(V_{IT+} - V_{IT-})$				50		mV
V	$V_{ID} = 200 \text{ mV}, I_O = -8 \text{ mA}, \text{ See Figure 6}$		e Figure 6	4.0			V
Vo	Output voltage	$V_{ID} = -200 \text{ mV}, I_O = 8 \text{ mA}, Sec.$	e Figure 6			0.3	v
		$V_A \text{ or } V_B = 12 \text{ V}$			0.20	0.3	
1	Due investorement	$V_A \text{ or } V_B = 12 \text{ V}, V_{CC} = 0 \text{ V}$	Other input		0.24	0.4	
I _A or I _B	Bus input current	$V_A \text{ or } V_B = -7 \text{ V}$	at 0 V	-0.35	-0.19		mA
		$V_A \text{ or } V_B = -7 \text{ V}, V_{CC} = 0 \text{ V}$		-0.25	-0.14		
I _{CC}	Supply current	D at 0 V or V_{CC} and No Load				2.7	mA

(1) All typical values are at 25°C and with a 5-V supply.

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN TYF	⁽¹⁾ MAX	
t _{PLH}	Propagation delay time, low-to-high-level output			24 40	
t _{PHL}	Propagation delay time, high-to-low-level output	V _I = 0 V to 3 V, C _L = 15 pF, See Figure 7		24 40	ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})			5	5
t _{sk(pp)} ⁽²⁾	Part-to-part skew			5	ns
t _r	Output signal rise time	C 15 pE Soo Eiguro 7		2 4	l ns
t _f	Output signal fall time	- C _L = 15 pF, See Figure 7		2 4	l ns

All typical values are at 25°C and with a 5-V supply
 t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

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THERMAL CHARACTERISTICS

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over operating free-air temperature range unless otherwise noted⁽¹⁾

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
0	Junction-to-ambient thermal resistance ⁽²⁾	Low-K board ⁽³⁾ , No airflow	230.8 135.1			00.000
θ_{JA}	Junction-to-ambient thermal resistance	High-K board ⁽⁴⁾ , No airflow				°C/W
θ_{JB}	Junction-to-board thermal resistance	High-K board		44.4		°C/W
θ_{JC}	Junction-to-case thermal resistance	No board		43.5		°C/W
P_D	Device power dissipation	R_L = 60 Ω , C_L = 50 pF, Input to D a 50% duty cycle square wave at indicated signaling rate			420	mW
Ŧ	A seletion to the terms and the	Low-K board, No airflow	-40		55	
IA	Ambient air temperature	High-K board, No airflow	-40		85	°C
T_{JSD}	Thermal shutdown junction temperature			165		°C

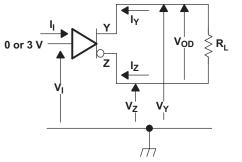
(1) See Application Information section for an explanation of these parameters.

(2) The intent of θ_{JA} specification is solely for a thermal performance comparison of one package to another in a standardized environment. This methodology is not meant to and will not predict the performance of a package in an application-specific environment.

(3) In accordance with the Low-K thermal metric definitions of EIA/JESD51-3.

(4) In accordance with the High-K thermal metric definitions of EIA/JESD51-7.

PARAMETER MEASUREMENT INFORMATION



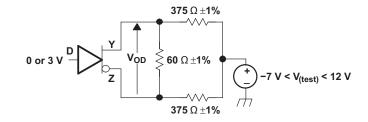


Figure 1. Driver V_{OD} Test Circuit: Voltage and Current Definitions



VOD(RING) is measured at four points on the output waveform, corresponding to overshoot and undershoot from the VOD(H) and VOD(L) steady state values.

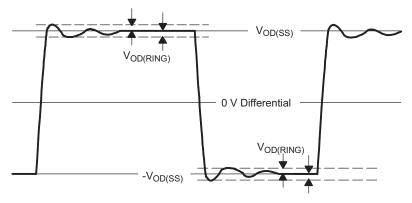


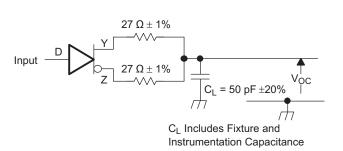
Figure 3. V_{OD(RING)} Waveform and Definitions

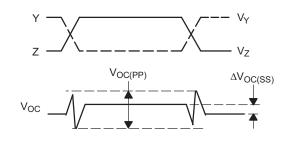
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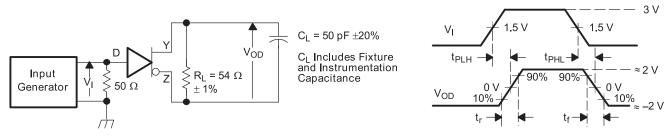
PARAMETER MEASUREMENT INFORMATION (continued)





Input: PRR = 500 kHz, 50% Duty Cycle,t r<6ns, tf<6ns, Z_O = 50 Ω

Figure 4. Test Circuit and Definitions for the Driver Common-Mode Output Voltage



Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6 \text{ ns}$, $t_f < 6 \text{ ns}$, $Z_0 = 50 \Omega$

Figure 5. Driver Switching Test Circuit and Voltage Waveforms

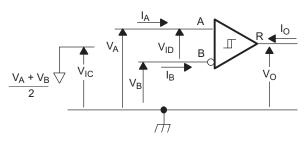
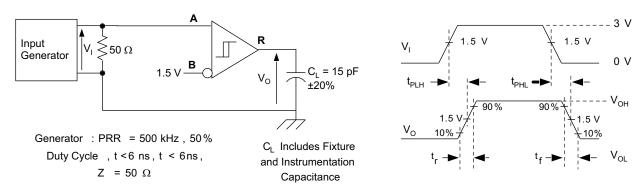


Figure 6. Receiver Voltage and Current Definitions







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PARAMETER MEASUREMENT INFORMATION (continued)

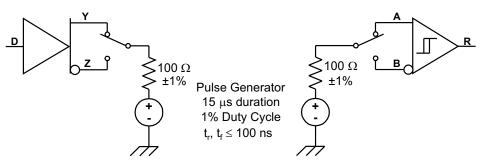
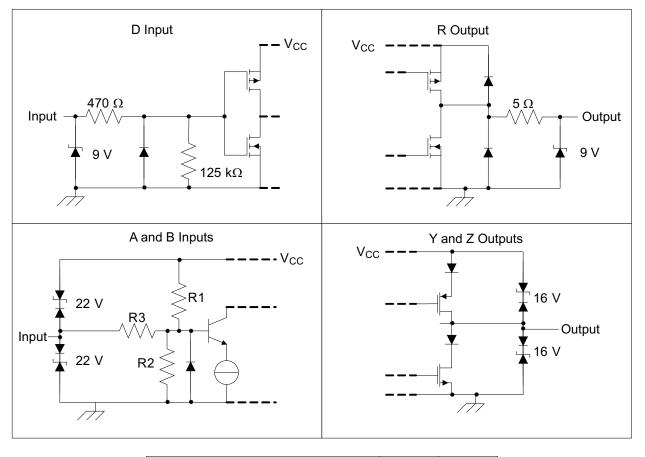


Figure 8. Test Circuit, Transient Overvoltage Test

FUNCTION TABLES

DRIVER			RECEIVER			
INPUT	OUTPUTS		OUTPUTS DIFFERENTIAL INF		DIFFERENTIAL INPUTS	OUTPUTS
D	Y	Z	$V_{ID} = V_A - V_B$	R		
Н	Н	L	$V_{ID} \leq -0.2 V$	L		
L	L	Н	$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$?		
Open	L	Н	$0.2 \text{ V} \leq \text{V}_{\text{ID}}$	Н		





EQUIVALENT INPUT	AND OUTPUT SCHEM	MATIC DIAGRAMS
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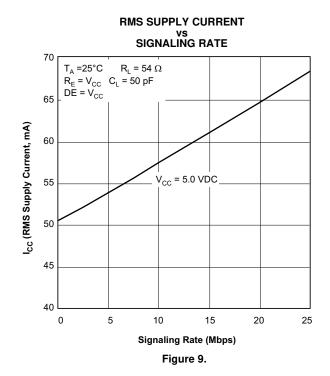
	R1/R2	R3
SN65HVD179 9	9 kΩ	45 kΩ

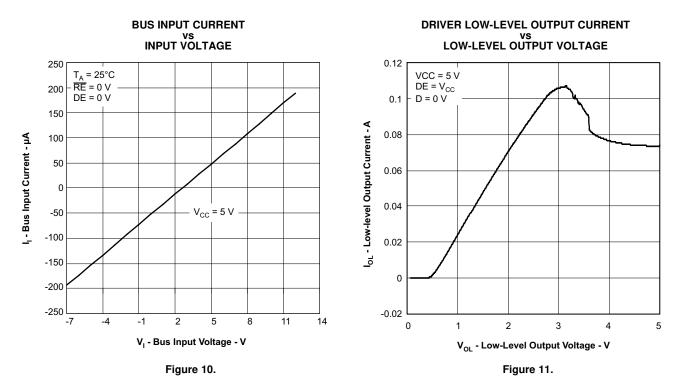
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TYPICAL CHARACTERISTICS





I_{OH} - High-level Output Current - A

TYPICAL CHARACTERISTICS (continued) DRIVER HIGH-LEVEL OUTPUT CURRENT DRIVER DIFFERENTIAL OUTPUT VOLTAGE VS HIGH-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE 2.9 VCC = 5 V $DE = V_{CC}$ V_{cc} = 5 V DE at V_{CC} D = 0 V2.8 V_{oD} - Driver Differential Voltage - V D at V_{CC} 2.7 2.6 2.5 2.4

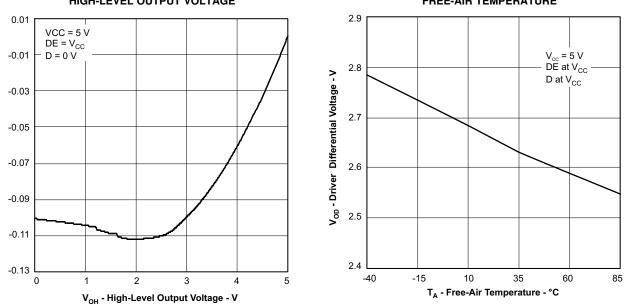
Figure 12.

Figure 13.

VS SUPPLY VOLTAGE 60 T_A = 25°C $R_L = 54 \Omega$ 50 D = V_{CC} DE = V_{CC} Io - Driver Output Current - mA 40 30 20 10 0 3 0 1 2 4 5 6 V_{cc} - Supply Voltage - V)







DRIVER OUTPUT CURRENT



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APPLICATION INFORMATION

THERMAL CHARACTERISTICS OF IC PACKAGES

 θ_{JA} (Junction-to-Ambient Thermal Resistance) is defined as the difference in junction temperature to ambient temperature divided by the operating power.

 θ_{JA} is not a constant and is a strong function of:

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

 θ_{JA} can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures. θ_{JA} is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-K board gives *average* in-use condition thermal performance, and it consists of a single copper trace layer 25 mm long and 2-oz thick. The high-K board gives best *case* in-use condition, and it consists of two 1-oz buried power planes with a single copper trace layer 25 mm long and 2-oz thick. A 4% to 50% difference in θ_{JA} can be measured between these two test cards

 θ_{JC} (Junction-to-Case Thermal Resistance) is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

 θ_{JC} is a useful thermal characteristic when a heatsink applied to package. It is *not* a useful characteristic to predict junction temperature because it provides pessimistic numbers if the case temperature is measured in a nonstandard system and junction temperatures are backed out. It can be used with θ_{JB} in 1-dimensional thermal simulation of a package system.

 θ_{JB} (Junction-to-Board Thermal Resistance) is defined as the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure. θ_{JB} is only defined for the high-K test card.

 θ_{JB} provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system, see Figure 15.

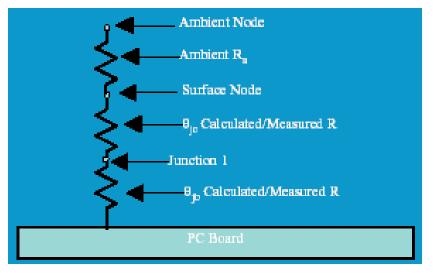


Figure 15. Thermal Resistance



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN65HVD179D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP179	
SN65HVD179DG4	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP179	
SN65HVD179DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP179	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

29-Mar-2023

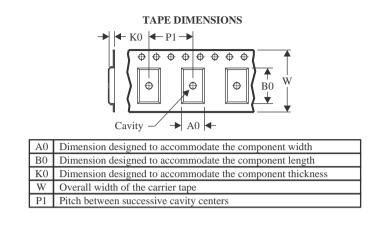


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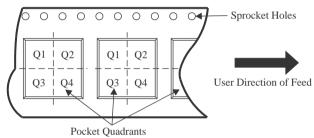
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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



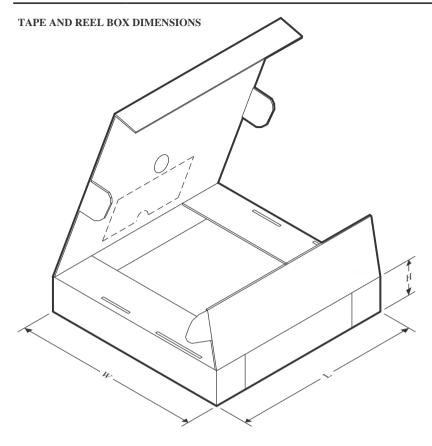
*All dimensions are nominal	

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD179DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

3-Jun-2022



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD179DR	SOIC	D	8	2500	356.0	356.0	35.0

TEXAS INSTRUMENTS

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3-Jun-2022

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65HVD179D	D	SOIC	8	75	506.6	8	3940	4.32
SN65HVD179DG4	D	SOIC	8	75	506.6	8	3940	4.32

D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- This dimension does not include interlead flash.
 Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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